

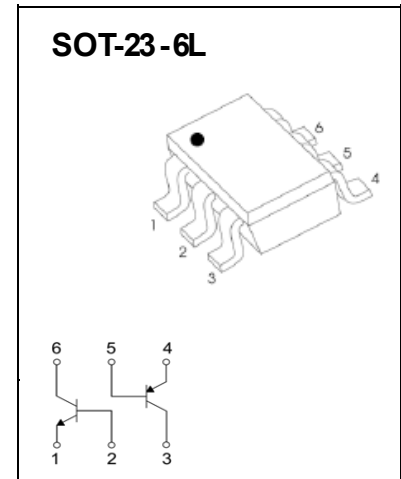
Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+PNP)

FEATURES

- Epitaxial Die Construction
- Two isolated NPN/PNP(BC817W+BC807W) Transistors in one package

MAKING: N4



MAXIMUM RATINGS TR1 (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	0.5	A
P _C	Collector Dissipation	0.2	W
R _{θJA}	Thermal Resistance from Junction to Ambient	625	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

CHARACTERISTICS of TR1 (NPN Transistor) (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =1μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =20V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =1V, I _C =100mA	160		400	
	h _{FE(2)}	V _{CE} =1V, I _C =500mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500mA, I _B =50mA			0.7	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =500mA, I _B =50mA			1.2	V
Base-emitter voltage	V _{BE(ON)}	V _{CE} =1V, I _C =500mA			1.2	V
Transition frequency	f _T	V _{CE} =5V, I _C =10mA, f=100MHz	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, f=1MHz			5	pF

MAXIMUM RATINGS TR2 ($T_a=25^\circ\text{C}$ unless otherwise noted)

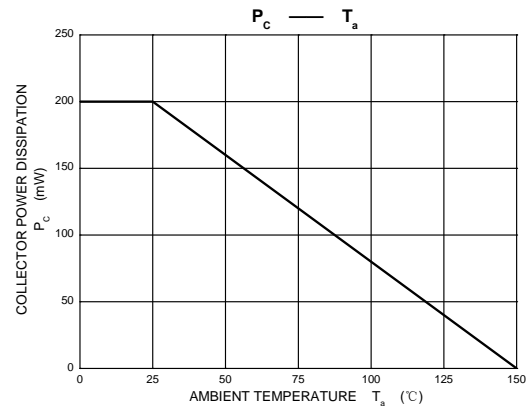
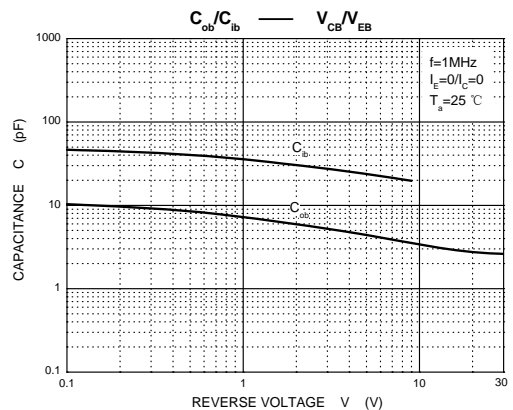
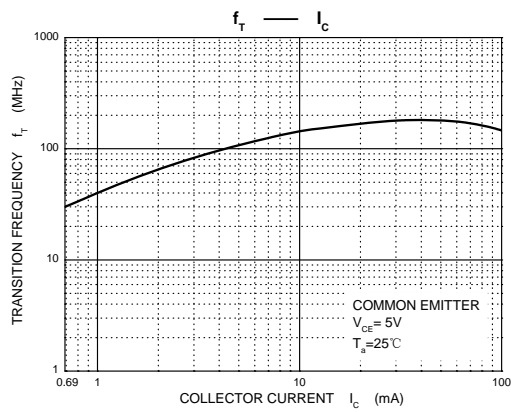
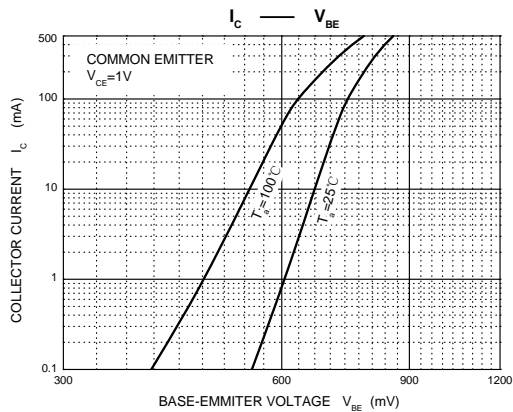
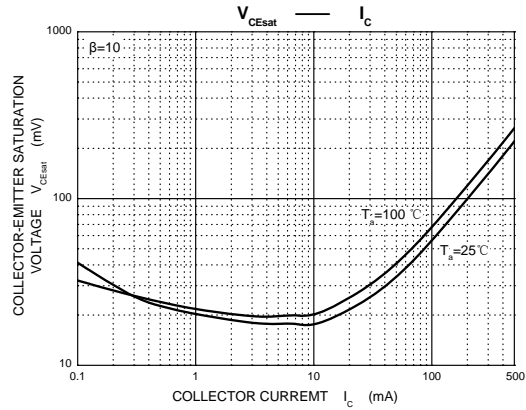
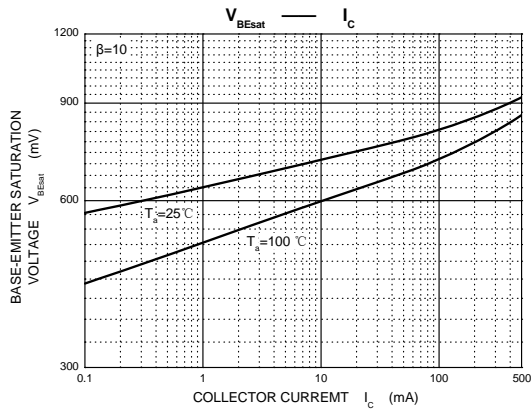
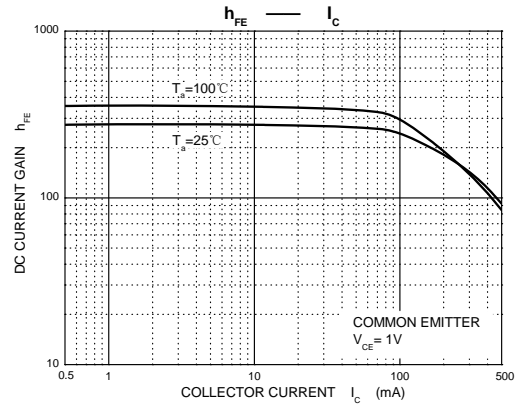
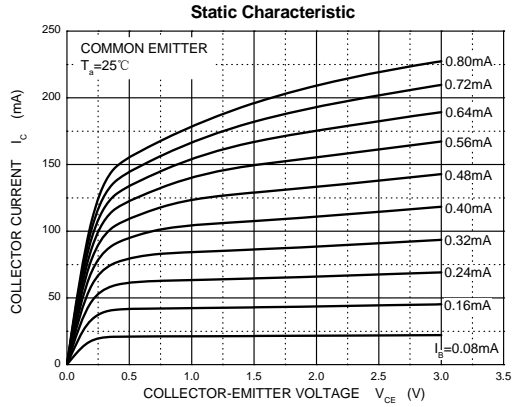
Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-500	mA
P_C	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	417	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

CHARACTERISTICS of TR2 (PNP Transistor) ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_C=-10\mu\text{A}, I_E=0$	-50		V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=-10\text{mA}, I_B=0$	-45		V
Emitter-base breakdown voltage	V_{EBO}	$I_E=-1\mu\text{A}, I_C=0$	-5		V
Collector cut-off current	I_{CB0}	$V_{CB}=-20\text{V}, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20\text{V}, I_B=0$		-0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	160	400	
	$h_{FE(2)}$	$V_{CE}=-1\text{V}, I_C=-500\text{mA}$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$		-0.7	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE}=-1\text{V}, I_C=-500\text{mA}$		-1.2	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$ $f=100\text{MHz}$	80		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, f=1\text{MHz}$		10	pF

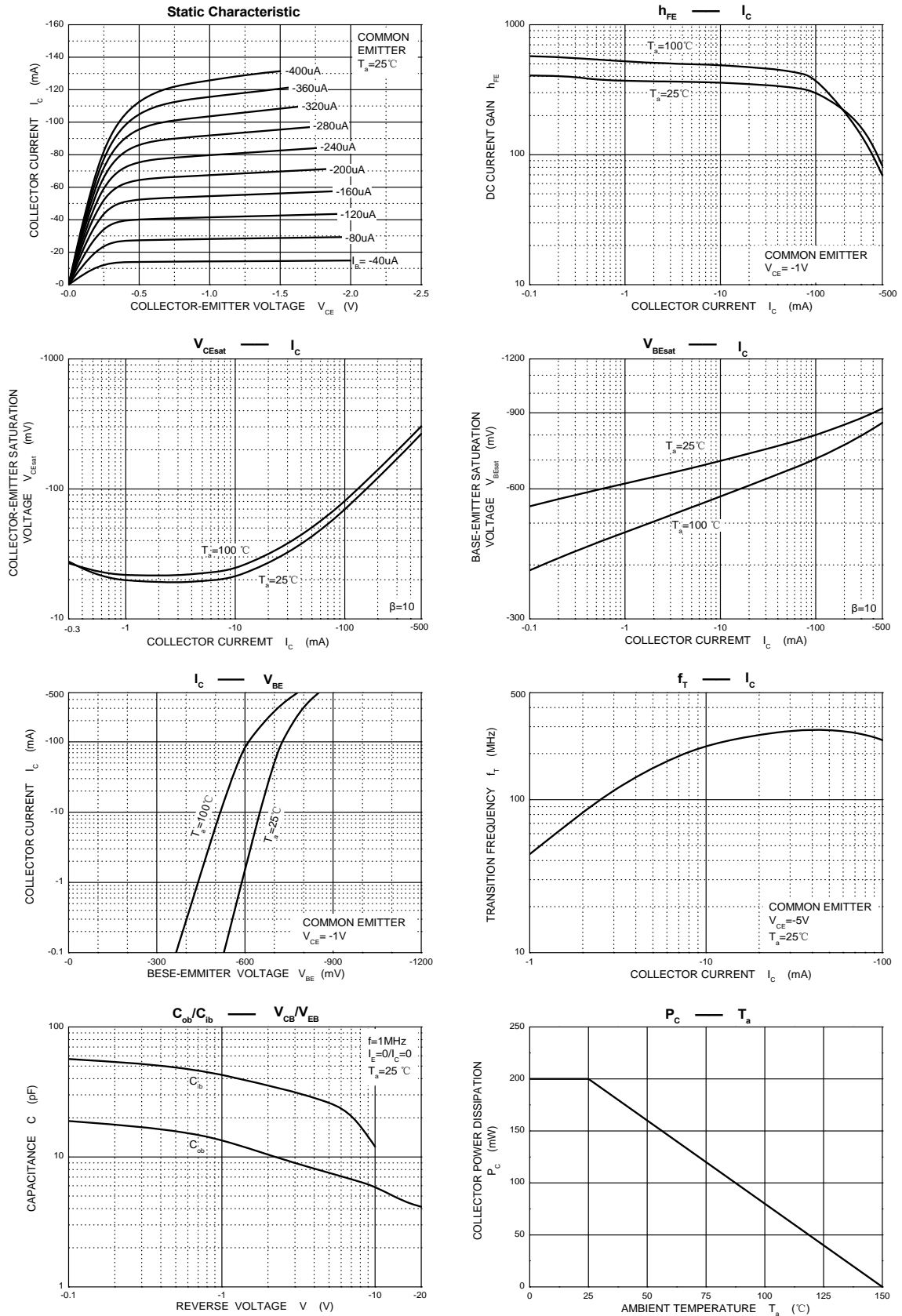
Typical Characteristics

BC817DPN/TR1

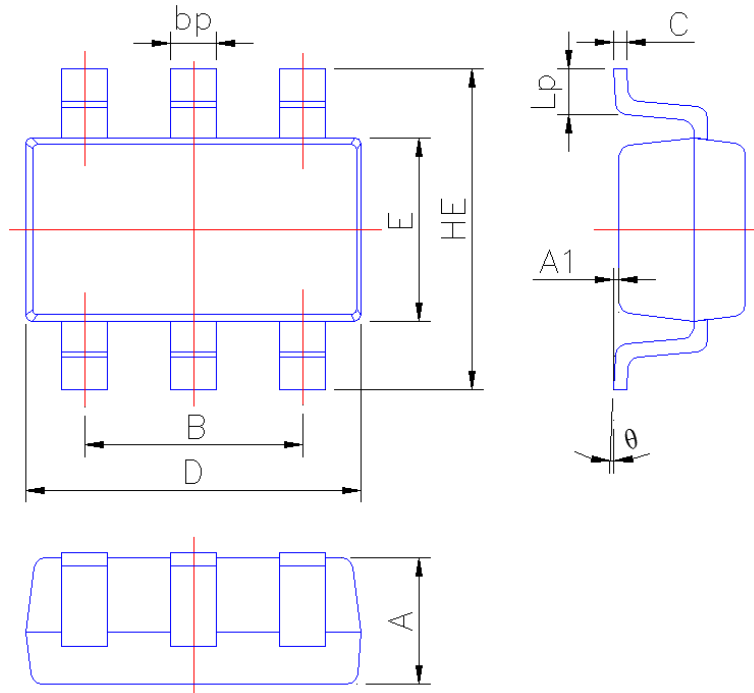


Typical Characteristics

BC807DPN/TR2



SOT-23-6L Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	1.05	1.20
A1	0.010	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.09	0.15
D	2.80	3.00
E	1.50	1.70
HE	2.60	3.00
Lp	0.25	0.55
θ	2°	6°